## Dual 2-Input NOR Gate

## NL27WZ02

The NL27WZ02 is a high performance dual 2-input NOR Gate operating from a 1.65 V to 5.5 V supply.

## Features

- Designed for 1.65 V to $5.5 \mathrm{~V} \mathrm{~V}_{\mathrm{CC}}$ Operation
- $2.5 \mathrm{~ns} \mathrm{t}_{\mathrm{PD}}$ at $\mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}$ (typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I IFFF Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in US8, UDFN8 and UQFN8 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant


Figure 1. Logic Symbol


ON Semiconductor ${ }^{\circledR}$
www.onsemi.com


ORDERING INFORMATION
See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

## NL27WZ02



Figure 2. Pinout

| PIN ASSIGNMENT (US8 / UDFN8) |  | PIN ASSIGNMENT (UQFN8) |  |
| :---: | :---: | :---: | :---: |
| Pin | Function | Pin | Function |
| 1 | A1 | 1 | Y1 |
| 2 | B1 | 2 | B2 |
| 3 | Y2 | 3 | A2 |
| 4 | GND | 4 | GND |
| 5 | A2 | 5 | Y2 |
| 6 | B2 | 6 | B1 |
| 7 | Y1 | 7 | A1 |
| 8 | $\mathrm{V}_{\mathrm{CC}}$ | 8 | $\mathrm{V}_{\mathrm{CC}}$ |

## NL27WZ02

MAXIMUM RATINGS

| Symbol | Characteristics | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | -0.5 to +6.5 | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage | -0.5 to +6.5 | V |
|  | DC Output Voltage <br> Active-Mode (High or Low State) <br> Tri-State Mode (Note 1) <br> Power-Down Mode ( $\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}$ ) | $\begin{gathered} -0.5 \text { to } \mathrm{V}_{\mathrm{CC}}+0.5 \\ -0.5 \text { to }+6.5 \\ -0.5 \text { to }+6.5 \end{gathered}$ | V |
| $\mathrm{I}_{\mathrm{IK}}$ | DC Input Diode Current $\quad \mathrm{V}_{\text {IN }}<\mathrm{GND}$ | -50 | mA |
| IOK | DC Output Diode Current $\quad$ VOUT < GND | -50 | mA |
| Iout | DC Output Source/Sink Current | $\pm 50$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ or $\mathrm{I}_{\mathrm{GND}}$ | DC Supply Current per Supply Pin or Ground Pin | $\pm 100$ | mA |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 secs | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Junction Temperature Under Bias | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ | $\begin{array}{lr}\text { Thermal Resistance (Note 2) } & \text { US8 } \\ \text { UQFN8 } \\ \text { UDFN8 }\end{array}$ | $\begin{aligned} & 250 \\ & 210 \\ & 231 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $P_{\text {D }}$ | $\begin{array}{lr}\text { Power Dissipation in Still Air } & \text { US8 } \\ & \text { UQFN8 } \\ \text { UDFN8 }\end{array}$ | $\begin{aligned} & 500 \\ & 595 \\ & 541 \end{aligned}$ | mW |
| MSL | Moisture Sensitivity | Level 1 | - |
| $\mathrm{F}_{\mathrm{R}}$ | Flammability Rating Oxygen Index: 28 to 34 | UL 94 V-0 @ 0.125 in | - |
| $\mathrm{V}_{\text {ESD }}$ | ESD Withstand Voltage (Note 3) $\begin{array}{r}\text { Human Body Model } \\ \text { Charged Device Model }\end{array}$ | $\begin{aligned} & 2000 \\ & 1000 \end{aligned}$ | V |
| ILatchup | Latchup Performance (Note 4) | $\pm 100$ | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm -by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to

EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Characteristics |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage |  | 1.65 | 5.5 | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage |  | 0 | 5.5 | V |
| $\mathrm{V}_{\text {OUT }}$ | DC Output Voltage | Active-Mode (High or Low State) <br> Tri-State Mode (Note 1) <br> Power-Down Mode ( $\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}$ ) | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{CC}} \\ & 5.5 \\ & 5.5 \end{aligned}$ |  |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=1.65 \mathrm{~V} \text { to } 1.95 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{CC}}=2.3 \mathrm{~V} \text { to } 2.7 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V} \text { to } 3.6 \mathrm{~V} \text { to } 5.5 \mathrm{~V} \end{gathered}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & 0 \end{aligned}$ | $\begin{gathered} 20 \\ 20 \\ 10 \\ 5 \end{gathered}$ | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $-55^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 125^{\circ} \mathrm{C}$ |  | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | High-Level Input Voltage |  | 1.65 to 1.95 | $0.65 \mathrm{~V}_{\mathrm{CC}}$ | - | - | $0.65 \mathrm{~V}_{\mathrm{CC}}$ | - | V |
|  |  |  | 2.3 to 5.5 | $0.70 \mathrm{~V}_{\mathrm{CC}}$ | - | - | $0.70 \mathrm{~V}_{\mathrm{CC}}$ | - |  |
| $\mathrm{V}_{\text {IL }}$ | Low-Level Input Voltage |  | 1.65 to 1.95 | - | - | $0.35 \mathrm{~V}_{\mathrm{CC}}$ | - | $0.35 \mathrm{~V}_{\mathrm{CC}}$ | V |
|  |  |  | 2.3 to 5.5 | - | - | $0.30 \mathrm{~V}_{\mathrm{CC}}$ | - | $0.30 \mathrm{~V}_{\mathrm{CC}}$ |  |
| $\mathrm{V}_{\mathrm{OH}}$ | High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{IOH}_{\mathrm{OH}}=-100 \mu \mathrm{AA} \\ & \mathrm{I}_{\mathrm{OH}}=-4 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-12 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-16 \mathrm{~mA} \\ & \mathrm{IOH}_{\mathrm{OH}}=-24 \mathrm{~mA} \\ & \mathrm{I}^{2} \mathrm{~mA} \end{aligned}$ | 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5 | $\mathrm{V}_{\mathrm{CC}}-0.1$ 1.29 1.9 2.2 2.4 2.3 3.8 | $\begin{aligned} & \mathrm{V}_{\mathrm{cc}} \\ & 1.4 \\ & 2.1 \\ & 2.4 \\ & 2.7 \\ & 2.5 \\ & 4.0 \end{aligned}$ |  | $\mathrm{V}_{\mathrm{CC}}-0.1$ 1.29 1.9 2.2 2.4 2.3 3.8 |  | V |
| $\mathrm{V}_{\text {OL }}$ | Low-Level Output Voltage | $\begin{array}{\|l} \hline \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IH}} \mathrm{or} \mathrm{~V}_{\mathrm{IL}} \\ \mathrm{I}_{\mathrm{OL}}=100 \mu \mathrm{uA} \\ \mathrm{I}_{\mathrm{OL}}=4 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{OL}}=8 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{OL}}=12 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{OL}}=16 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{OL}}=24 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{OL}}=32 \mathrm{~mA} \\ \hline \end{array}$ | 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5 | $\begin{aligned} & - \\ & - \\ & - \\ & - \\ & - \end{aligned}$ | $\begin{gathered} - \\ 0.08 \\ 0.2 \\ 0.22 \\ 0.28 \\ 0.38 \\ 0.42 \end{gathered}$ | $\begin{gathered} 0.1 \\ 0.24 \\ 0.3 \\ 0.4 \\ 0.4 \\ 0.55 \\ 0.55 \end{gathered}$ |  | $\begin{gathered} 0.1 \\ 0.24 \\ 0.3 \\ 0.4 \\ 0.4 \\ 0.55 \\ 0.55 \end{gathered}$ | V |
| 1 N | Input Leakage Current | $\mathrm{V}_{\text {IN }}=5.5 \mathrm{~V}$ or GND | 1.65 to 5.5 | - | - | $\pm 0.1$ | - | $\pm 1.0$ | $\mu \mathrm{A}$ |
| IOFF | Power Off Leakage Current | $\begin{aligned} & \mathrm{V}_{\text {IN }}=5.5 \mathrm{~V} \text { or } \\ & \mathrm{V}_{\text {OUT }}=5.5 \mathrm{~V} \end{aligned}$ | 0 | - | - | 1.0 | - | 10 | $\mu \mathrm{A}$ |
| Icc | Quiescent Supply Current | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or GND | 5.5 | - | - | 1.0 | - | 10 | $\mu \mathrm{A}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | $\mathrm{V}_{\mathrm{cc}}(\mathrm{V})$ | Test Conditions | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $\mathrm{T}_{\mathrm{A}}=-55$ to $125^{\circ} \mathrm{C}$ |  | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max |  |
| $\begin{aligned} & \hline \mathrm{t}_{\mathrm{PLLH}}, \\ & \mathrm{t}_{\mathrm{PH}} \end{aligned}$ | Propagation Delay, (A or B) to Y | 1.65 to 1.95 | $\begin{aligned} & \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF} \\ & \mathrm{R}_{\mathrm{L}}=1 \mathrm{MQ} \\ & \mathrm{R}_{1}=\text { Open } \end{aligned}$ | - | 7.4 | 9.5 | - | 9.7 | ns |
|  |  | 2.3 to 2.7 |  | - | 3.3 | 5.4 | - | 5.8 |  |
|  |  | 3.0 to 3.6 |  | - | 2.6 | 3.9 | - | 4.3 |  |
|  |  | 4.5 to 5.5 |  | - | 1.9 | 3.1 | - | 3.3 |  |
|  |  | 3.0 to 3.6 | $\begin{aligned} & \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}, \\ & \mathrm{R}_{\mathrm{L}}=500 \Omega, \mathrm{R}_{1}=\text { Open } \end{aligned}$ | - | 3.2 | 4.8 | - | 5.2 |  |
|  |  | 4.5 to 5.5 |  | - | 2.5 | 3.7 | - | 4.0 |  |

## CAPACITIVE CHARACTERISTICS

| Symbol | Parameter | Condition | Typical | Units |
| :---: | :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Input Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 2.5 | pF |
| $\mathrm{C}_{\mathrm{OUT}}$ | Output Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 2.5 | pF |
| $\mathrm{C}_{\mathrm{PD}}$ | Power Dissipation Capacitance <br> (Note 5) | $10 \mathrm{MHz}, \mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ <br> $10 \mathrm{MHz}, \mathrm{V} \mathrm{CC}=5.5 \mathrm{~V}, \mathrm{~V} \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 9 | pF |

5. $\mathrm{C}_{\mathrm{PD}}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $\mathrm{I}_{\mathrm{CC}(\mathrm{OPR})}=\mathrm{C}_{\mathrm{PD}} \bullet \mathrm{V}_{\mathrm{CC}} \bullet \mathrm{f}_{\mathrm{in}}+\mathrm{I}_{\mathrm{CC}}$. $\mathrm{C}_{\mathrm{PD}}$ is used to determine the no-load dynamic power consumption; $\mathrm{P}_{\mathrm{D}}=\mathrm{C}_{\mathrm{PD}} \bullet \mathrm{V}_{\mathrm{CC}}{ }^{2} \bullet \mathrm{f}_{\mathrm{in}}+\mathrm{I}_{\mathrm{CC}} \bullet \mathrm{V}_{\mathrm{CC}}$.

$\mathrm{C}_{\mathrm{L}}$ includes probe and jig capacitance
$\mathrm{R}_{\mathrm{T}}$ is $\mathrm{Z}_{\text {OUT }}$ of pulse generator (typically $50 \Omega$ )
$\mathrm{f}=1 \mathrm{MHz}$
Figure 3. Test Circuit


Figure 4. Switching Waveforms

| $\mathbf{V}_{\mathbf{C C}}, \mathbf{v}$ | $\mathbf{V}_{\mathbf{m o}}, \mathbf{V}$ |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  |  |  | $\mathbf{t}_{\mathbf{P Z L}}, \mathbf{t}_{\mathbf{P L Z}}, \mathbf{t}_{\mathbf{P Z H}}, \mathbf{t}_{\mathbf{P H Z}}$ | $\mathbf{v}_{\mathbf{Y},} \mathbf{v}$ |
|  | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.15 |
| 2.3 to 2.7 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.15 |
| 3.0 to 3.6 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.3 |
| 4.5 to 5.5 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.3 |

DEVICE ORDERING INFORMATION

| Device | Packages | Specific Device Code | Pin 1 Orientation <br> (See below) | Shipping $^{\dagger}$ |
| :--- | :---: | :---: | :---: | :---: |
| NL27WZ02USG | US8 | L3 | Q4 | $3000 /$ Tape \& Reel |
| NL27WZ02MQ1TCG <br> (In Development) | UQFN8, $1.6 \times 1.6,0.5 \mathrm{P}$ | TBD | TBD | $3000 /$ Tape \& Reel |
| NL27WZ02MU1TCG | UDFN8, $1.95 \times 1.0,0.5 \mathrm{P}$ | AL | Q4 | $3000 /$ Tape \& Reel |
| NL27WZ02MU1TWG | UDFN8, $1.95 \times 1.0,0.5 \mathrm{P}$ | AM | Q 1 | $3000 /$ Tape \& Reel |
| NL27WZ02MU3TCG | UDFN8, $1.45 \times 1.0,0.35 \mathrm{P}$ | J | $\mathrm{Q4}$ | $3000 /$ Tape \& Reel |
| NL27WZ02MU2TCG | UDFN8, $1.6 \times 1.0,0.4 \mathrm{P}$ | AH | $\mathrm{Q4}$ | $3000 /$ Tape \& Reel |
| NL27WZ02MQ2TCG <br> (In Development) | UQFN8, $1.4 \times 1.2,0.4 \mathrm{P}$ | TBD | TBD | $3000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel
Direction of Feed


SCALE $4: 1$

strategy and soldertio detalls, pleaze
dominoad the ON Senconductor soldering and
Mounting Techniques Reference Manual,
Moonnoad the ON Senticoncuctor Soldering an
MOUNERRNHD.
NDTES:

1. DIMENSIONING AND TQLERANCING PER ANSI Y14.5M, 1982.
2. CINTRILLING DIMENSİN: MILLIMETERS
3. Dimensian a daes nat include mald flash, pratrusidn, ar Gate burr. mald flash, pratrusion, ar gate burr SHALL NOT EXCEED 0.14 ( $0.0055^{\circ}$ ) PER SIDE.
4. Dimensian b daes nat include interlead flash ar pratrusicn. interlead flash and pratrusinn shall nat EXCEED 0.14 ( $0.0055^{\circ}$ ) PER SIDE.
5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS DF $0.0076-0.0203$ MM ( $0.003-0.008^{\circ}$ ).
6. ALL TOLERANCE UNLESS $\quad$ aTHERWISE SPECIFIED $\pm 0.0508$ MM ( $0.000^{\circ}$ ).

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN. | MAX. | MIN | MAX. |
| A | 1.90 | 2.10 | 0.075 | 0.083 |
| B | 2.20 | 2.40 | 0.087 | 0.094 |
| C | 0.60 | 0.90 | 0.024 | 0.035 |
| D | 0.17 | 0.25 | 0.007 | 0.010 |
| F | 0.20 | 0.35 | 0.008 | 0.014 |
| G | 0.50 BSC |  | 0.020 BSC |  |
| H | 0.40 REF |  | 0.016 REF |  |
| J | 0.10 | 0.18 | 0.004 | 0.007 |
| K | 0.00 | 0.10 | 0.000 | 0.004 |
| L | 3.00 | 3.25 | 0.118 | 0.128 |
| M | $0{ }^{\circ}$ | $6^{\circ}$ | $0^{\circ}$ | $6^{\circ}$ |
| N | $0 \times$ | $10^{\circ}$ | $0^{\circ}$ | $10^{\circ}$ |
| P | 0.23 | 0.34 | 0.010 | 0.013 |
| R | 0.23 | 0.33 | 0.009 | 0.013 |
| S | 0.37 | 0.47 | 0.015 | 0.019 |
| U | 0.60 | 0.80 | 0.024 | 0.031 |
| V | 0.12 BSC |  | 0.005 BSC |  |

GENERIC MARKING DIAGRAM*


| XX | $=$ Specific Device Code |
| :--- | :--- |
| M | $=$ Date Code |
| - | $=$ Pb-Free Package |

(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-F r e e$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | US8 | PAGE 1 OF 1 |

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH

| BURRS AND MOLD FLA |
| :--- |


|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | IIN | MAX |
| A | 0.45 | 0.55 |
| A1 | 0.00 | 0.05 |
| A3 | 0.13 REF |  |
| b | 0.15 | 0.25 |
| D | 1.60 | BSC |
| E | 1.00 |  |
| BSC |  |  |
| e | 0.40 |  |
| L | 0.25 | 0.35 |
| L1 | 0.30 | 0.40 |

GENERIC
MARKING DIAGRAM*


X = Specific Device Code
M = Date Code
*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot " $\quad$ ", may or may not be present.

## RECOMMENDED

 SOLDERING FOOTPRINT*

DIMENSIONS: MILLIMETERS
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | UDFN8, 1.6X1, 0.4P |  | PAGE 1 OF 1 |

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED

TERMINAL AND IS MEASURED BETWEEN
0.15 AND 0.20 MM FROM TERMINAL TIP
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH


|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | 0.45 | 0.55 |
| A1 | 0.00 | 0.05 |
| A3 | 0.13 REF |  |
| b | 0.15 |  |
| D | 0.25 |  |
| E | 1.45 BSC |  |
| e | 0.35 |  |
| BSC |  |  |
| L | 0.25 | 0.35 |
| L1 | 0.30 | 0.40 |

GENERIC
MARKING DIAGRAM*

$X=$ Specific Device Code
M = Date Code
*This information is generic. Please refer to device data sheet for actual part marking.
$\mathrm{Pb}-$ Free indicator, "G" or microdot " $\cdot$ ", may or may not be present.

RECOMMENDED
SOLDERING FOOTPRINT*

*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | UDFN8, 1.45X1, 0.35P | PAGE 1 OF 1 |

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DATE 22 SEP 2020
NDTES:

1. DIMENSIDNING AND TDLERANCING PER ASME Y14.5M, 2009.
2. CONTRDLLING DIMENSICN: MILLIMETERS
3. DIMENSIDN b APPLIES TD PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FRDM THE TERMINAL TIP.
4. CDPLANARITY APPLIES TO TD ALL THE TERMINALS.
5. PACKAGE DIMENSIGNS EXCLUSIVE DF BURRS AND MILD FLASH.

PIN 1 REFERENCE TDP VIEW

DETAIL
B


| DIM | MILLIMETERS |  |  |
| :--- | :---: | :---: | :---: |
|  | MIN. | NDM. | MAX. |
| A | 0.45 | 0.50 | 0.55 |
| A1 | 0.00 | --- | 0.05 |
| A3 | 0.13 REF |  |  |
| b | 0.15 | 0.20 | 0.25 |
| D | 1.85 | 1.95 | 2.05 |
| E | 0.90 | 1.00 | 1.10 |
| e | 0.50 BSC |  |  |
| L | 0.25 | 0.30 | 0.35 |
| L1 | 0.30 | 0.35 | 0.40 |





BZTTGM VIEW NDTE 3

## GENERIC <br> MARKING DIAGRAM*



$$
\begin{aligned}
& X=\text { Specific Device Code } \\
& M=\text { Date Code }
\end{aligned}
$$

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present. Some products may not follow the Generic Marking.

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| :---: | :---: | :---: |
| DESCRIPTION: | UDFN8, 1.95X1.0, 0.5P | PAGE 1 OF 1 |

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